

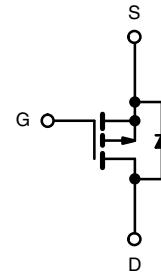
RSJ250P10TL-VB Datasheet

P-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ.)
- 100	0.040 at $V_{GS} = - 10$ V	- 37	54 nC
	0.050 at $V_{GS} = - 4.5$ V	- 32	

FEATURES

- TrenchFET® Power MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 100	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C) ^b	I_D	- 37	A
		- 29.5	
		- 10 ^{b, c}	
		- 8.2 ^{b, c}	
Pulsed Drain Current	I_{DM}	- 150	
Continuous Source Current (Diode Conduction)	I_S	- 50 ^a	
		- 6.75 ^{b, c}	
Avalanche Current	I_{AS}	- 35	
Single Pulse Avalanche Energy	E_{AS}	61	mJ
Maximum Power Dissipation	P_D	113.6	W
		72.7	
		6.9 ^{b, c}	
		4.4 ^{b, c}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Junction-to-Ambient	R_{thJA}	40	°C/W
Junction-to-Case (Drain)	R_{thJC}	2.1	

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. t = 10 s.

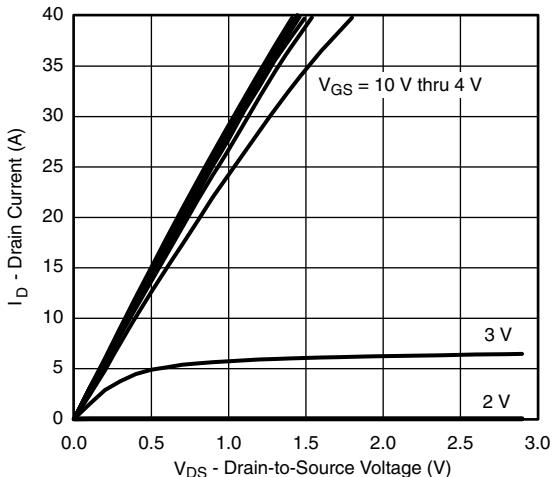
SPECIFICATIONS ($T_J = 25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-100			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250 \mu\text{A}$		-109		$\text{mV}/^\circ\text{C}$
$V_{GS(\text{th})}$ Temperature Coefficient	$\Delta V_{GS(\text{th})}/T_J$			5.9		
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$	-1		-3	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -100 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μA
		$V_{DS} = -100 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^\circ\text{C}$			-10	
On-State Drain Current ^a	$I_{D(\text{on})}$	$V_{DS} \geq 5 \text{ V}, V_{GS} = -10 \text{ V}$	-40			A
Drain-Source On-State Resistance ^a	$R_{DS(\text{on})}$	$V_{GS} = -10 \text{ V}, I_D = -9.2 \text{ A}$		0.040		Ω
		$V_{GS} = -4.5 \text{ V}, I_D = -7.7 \text{ A}$		0.050		
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15 \text{ V}, I_D = -9.2 \text{ A}$		38		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = -50 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		3800		pF
Output Capacitance	C_{oss}			185		
Reverse Transfer Capacitance	C_{rss}			135		
Total Gate Charge	Q_g	$V_{DS} = -50 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -9.2 \text{ A}$		106	160	nC
Gate-Source Charge	Q_{gs}	$V_{DS} = -50 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = -9.2 \text{ A}$		54	81	
Gate-Drain Charge	Q_{gd}			14		
Gate Resistance	R_g		$f = 1 \text{ MHz}$	26		
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DD} = -50 \text{ V}, R_L = 6.5 \Omega$ $I_D \approx -7.7 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$		4		Ω
Rise Time	t_r			15	25	ns
Turn-Off Delay Time	$t_{d(\text{off})}$			20	30	
Fall Time	t_f			110	165	
Turn-On Delay Time	$t_{d(\text{on})}$			100	150	ns
Rise Time	t_r			42	65	
Turn-Off Delay Time	$t_{d(\text{off})}$			160	240	
Fall Time	t_f			100	150	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25^\circ\text{C}$			-50	A
Pulse Diode Forward Current ^a	I_{SM}				-40	
Body Diode Voltage	V_{SD}	$I_S = -7.7 \text{ A}$		-0.8	-1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -7.7 \text{ A}, dI/dt = 100 \text{ A}/\mu\text{s}, T_J = 25^\circ\text{C}$		60	90	ns
Body Diode Reverse Recovery Charge	Q_{rr}			150	225	nC
Reverse Recovery Fall Time	t_a			46		ns
Reverse Recovery Rise Time	t_b			14		

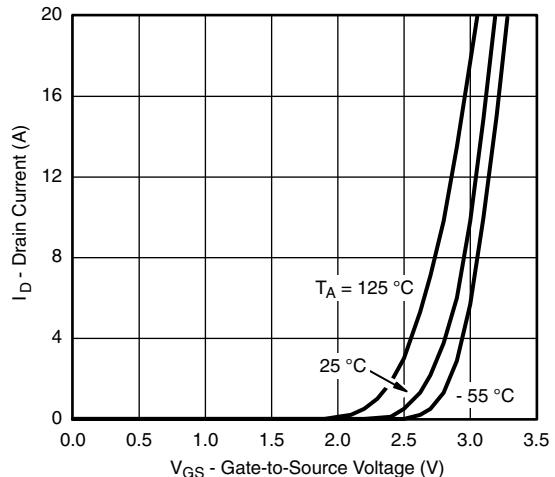
Notes:

a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

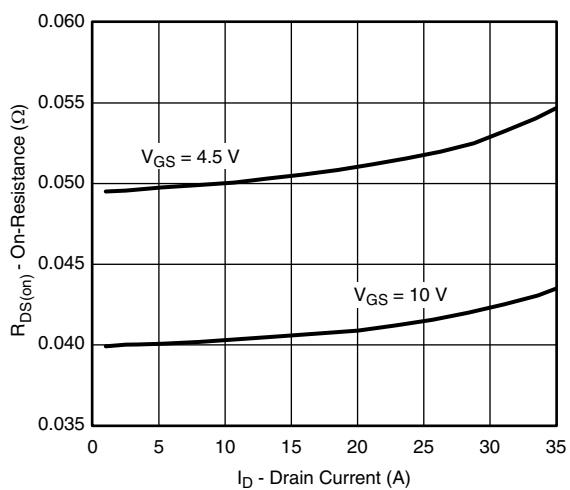
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


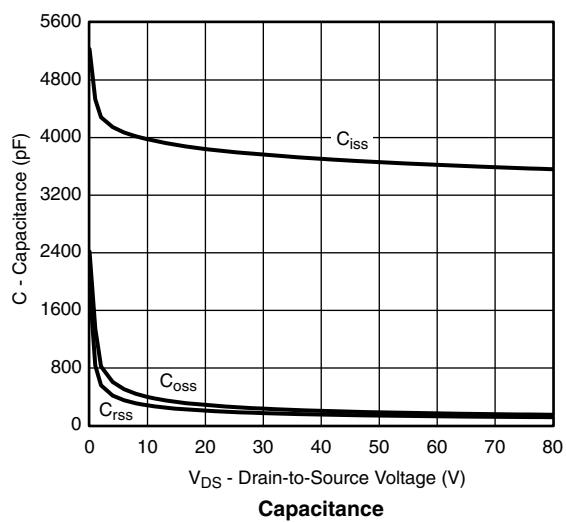
Output Characteristics



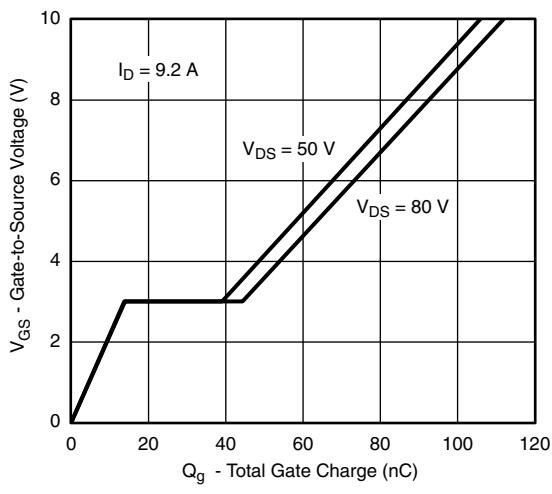
Transfer Characteristics



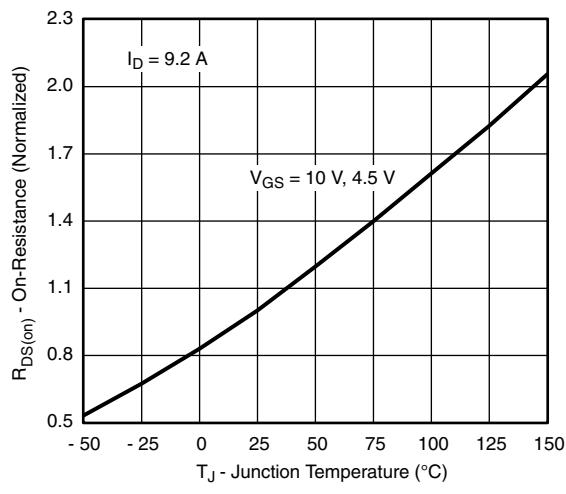
On-Resistance vs. Drain Current and Gate Voltage



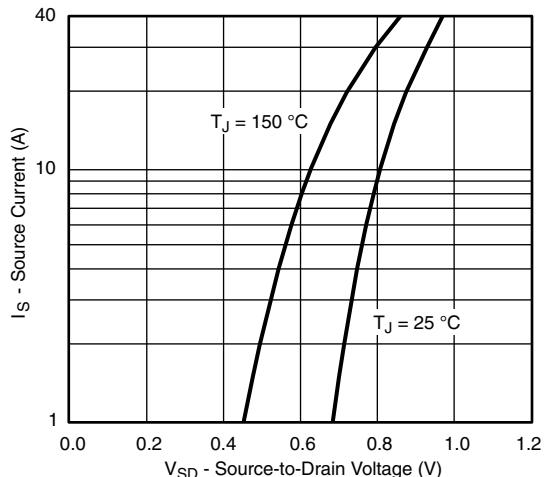
Capacitance



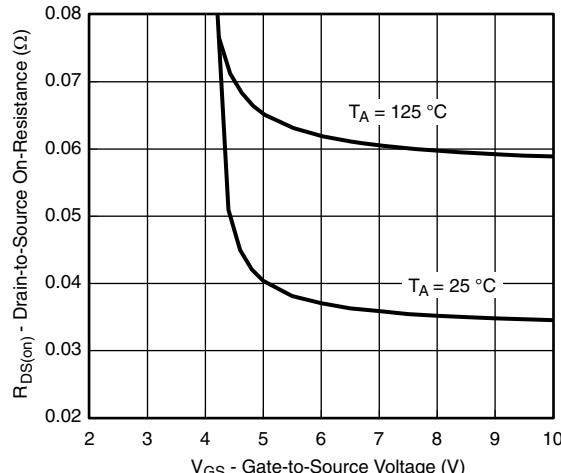
Gate Charge



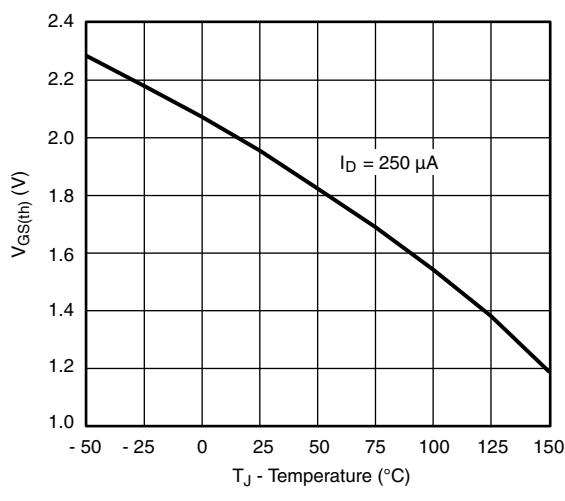
On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


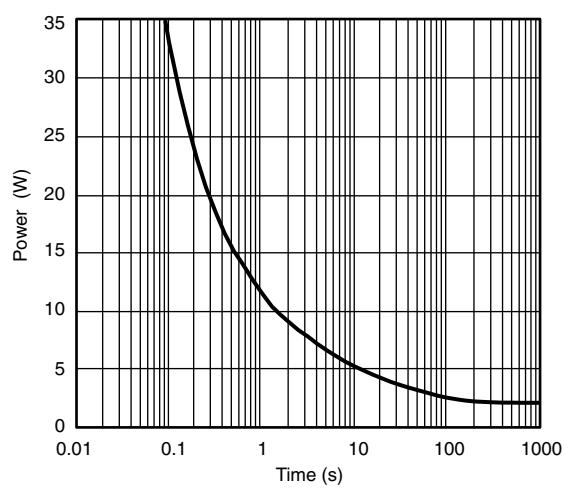
Source-Drain Diode Forward Voltage



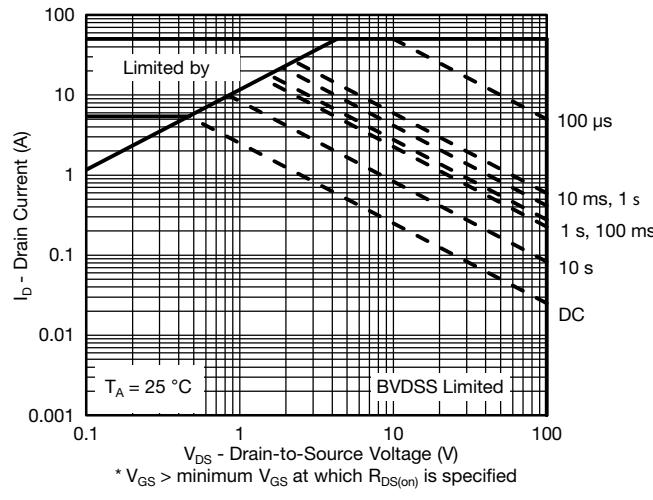
On-Resistance vs. Gate-to-Source Voltage



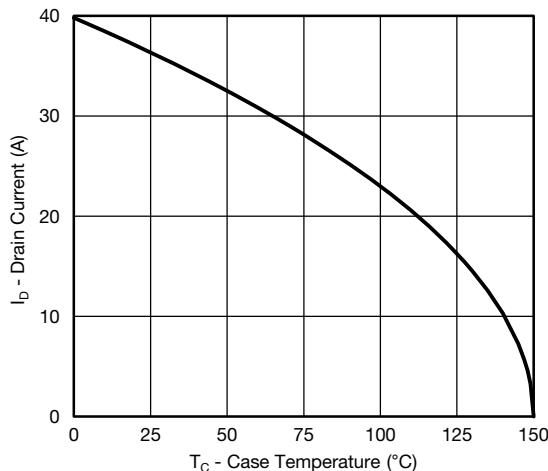
Threshold Voltage



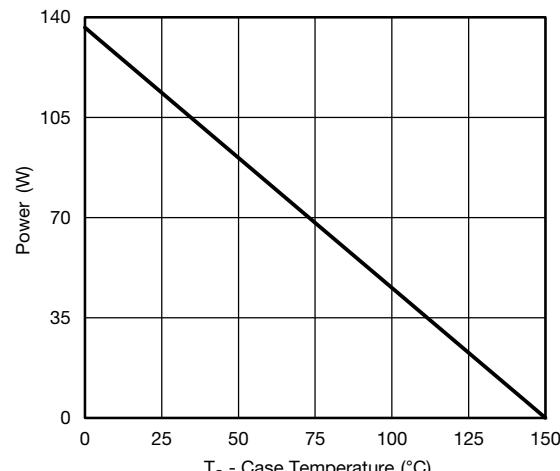
Single Pulse Power, Junction-to-Ambient



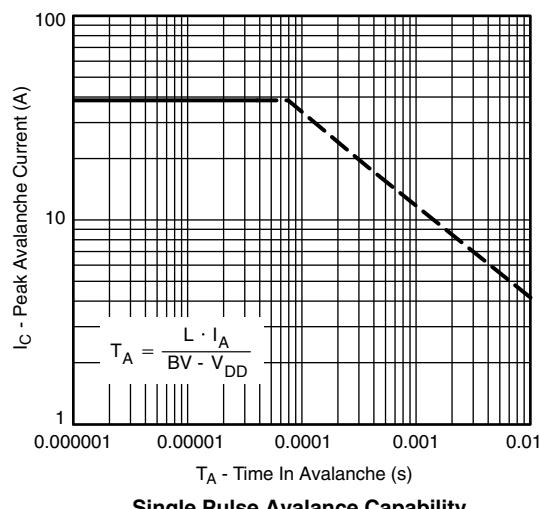
Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


Current Derating*

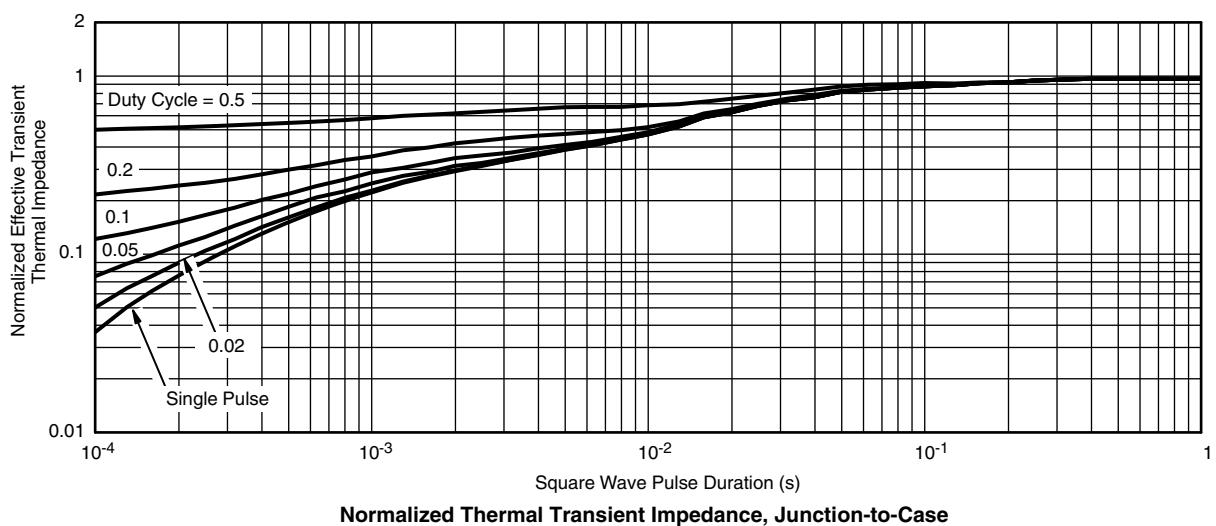
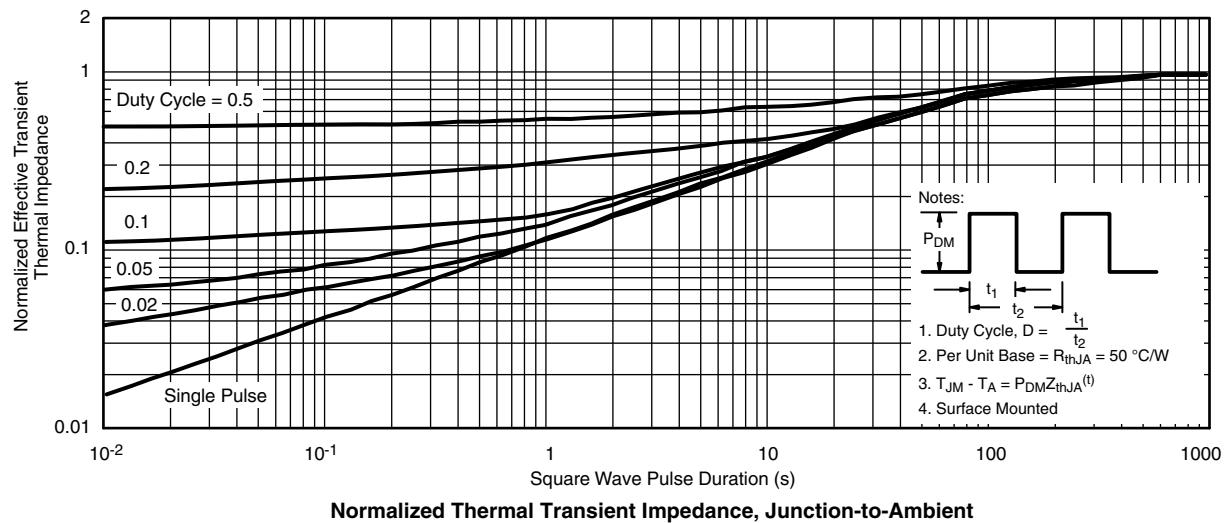


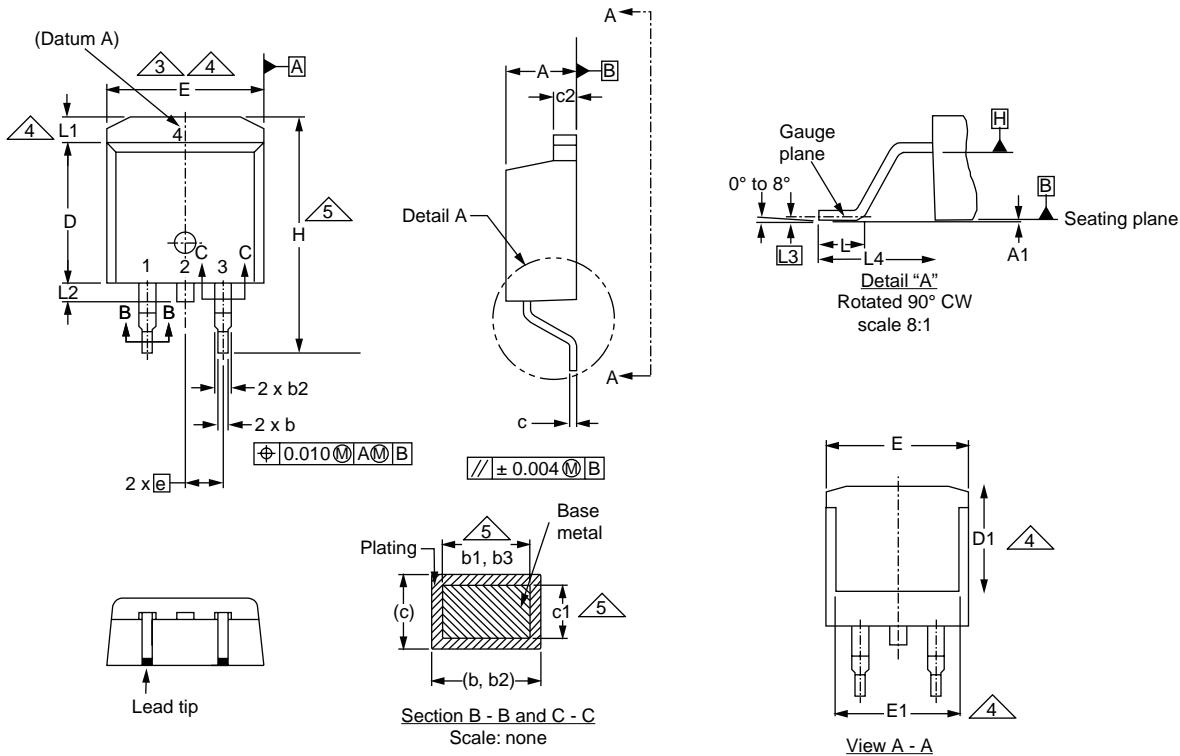
Single Pulse Power, Junction-to-Ambient



Single Pulse Avalanche Capability

* The power dissipation P_D is based on $T_{J(\max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


TO-263AB (HIGH VOLTAGE)

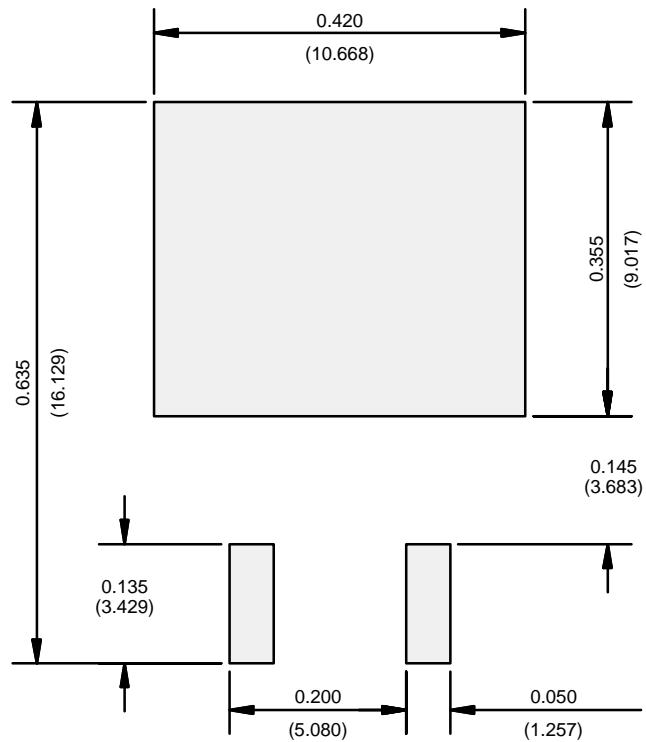
DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

ECN: S-82110-Rev. A, 15-Sep-08
 DWG: 5970

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead

Recommended Minimum Pads
Dimensions in Inches/(mm)

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